

PowerMOS transistor

Logic level FET

BUK565-60H

GENERAL DESCRIPTION

N-channel enhancement mode logic level field-effect power transistor in a plastic envelope suitable for surface mount applications. The device is intended for use in automotive and general purpose switching applications.

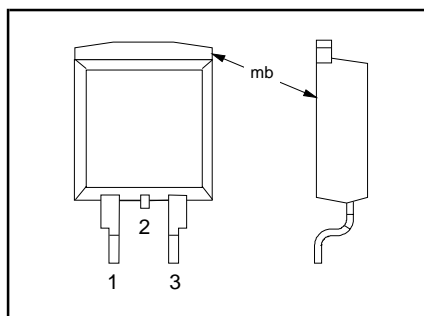
QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{DS}	Drain-source voltage	60	V
I_D	Drain current (DC)	41	A
P_{tot}	Total power dissipation	125	W
T_j	Junction temperature	175	°C
$R_{DS(ON)}$	Drain-source on-state resistance; $V_{GS} = 5\text{ V}$	38	mΩ

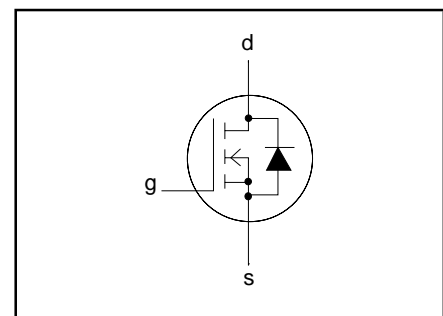
PINNING - SOT404

PIN	DESCRIPTION
1	gate
2	drain
3	source
mb	drain

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	Drain-source voltage	-	-	60	V
V_{DGR}	Drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	60	V
$\pm V_{GS}$	Gate-source voltage	-	-	15	V
$\pm V_{GSM}$	Non-repetitive gate-source voltage	$t_p \leq 50\ \mu\text{s}$	-	20	V
I_D	Drain current (DC)	$T_{mb} = 25\text{ }^\circ\text{C}$	-	41	A
I_D	Drain current (DC)	$T_{mb} = 100\text{ }^\circ\text{C}$	-	29	A
I_{DM}	Drain current (pulse peak value)	$T_{mb} = 25\text{ }^\circ\text{C}$	-	164	A
P_{tot}	Total power dissipation	$T_{mb} = 25\text{ }^\circ\text{C}$	-	125	W
T_{stg}	Storage temperature	-	-55	175	°C
T_j	Junction temperature	-	-	175	°C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-mb}$	Thermal resistance junction to mounting base		-	1.2	K/W
$R_{th\ j-a}$	Thermal resistance junction to ambient	minimum footprint, FR4 board (see Fig. 18)	50	-	K/W

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STATIC CHARACTERISTICS

 $T_{mb} = 25\text{ °C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 0.25\text{ mA}$	60	-	-	V
$V_{GS(TO)}$	Gate threshold voltage	$V_{DS} = V_{GS}; I_D = 1\text{ mA}$	1.0	1.5	2.0	V
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 60\text{ V}; V_{GS} = 0\text{ V}; T_j = 25\text{ °C}$	-	1	10	μA
I_{DSS}	Zero gate voltage drain current	$V_{DS} = 60\text{ V}; V_{GS} = 0\text{ V}; T_j = 125\text{ °C}$	-	0.1	1.0	mA
I_{GSS}	Gate source leakage current	$V_{GS} = \pm 15\text{ V}; V_{DS} = 0\text{ V}$	-	10	100	nA
$R_{DS(ON)}$	Drain-source on-state resistance	$V_{GS} = 5\text{ V}; I_D = 20\text{ A}$	-	25	38	m Ω

DYNAMIC CHARACTERISTICS

 $T_{mb} = 25\text{ °C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
g_{fs}	Forward transconductance	$V_{DS} = 25\text{ V}; I_D = 20\text{ A}$	11	20	-	S
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 25\text{ V}; f = 1\text{ MHz}$	-	1200	1750	pF
C_{oss}	Output capacitance		-	470	600	pF
C_{rss}	Feedback capacitance		-	180	275	pF
$t_{d\ on}$	Turn-on delay time	$V_{DD} = 30\text{ V}; I_D = 3\text{ A};$ $V_{GS} = 5\text{ V}; R_{GS} = 50\ \Omega;$ $R_{gen} = 50\ \Omega$	-	25	40	ns
t_r	Turn-on rise time		-	120	150	ns
$t_{d\ off}$	Turn-off delay time		-	160	220	ns
t_f	Turn-off fall time		-	110	145	ns
L_d	Internal drain inductance	Measured from contact screw on tab to centre of die	-	3.5	-	nH
L_d	Internal drain inductance	Measured from drain lead 6 mm from package to centre of die	-	4.5	-	nH
L_s	Internal source inductance	Measured from source lead 6 mm from package to source bond pad	-	7.5	-	nH

REVERSE DIODE LIMITING VALUES AND CHARACTERISTICS

 $T_{mb} = 25\text{ °C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{DR}	Continuous reverse drain current	-	-	-	41	A
I_{DRM}	Pulsed reverse drain current	-	-	-	164	A
V_{SD}	Diode forward voltage	$I_F = 41\text{ A}; V_{GS} = 0\text{ V}$	-	0.95	2.0	V
t_{rr}	Reverse recovery time	$I_F = 41\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s};$ $V_{GS} = 0\text{ V}; V_R = 30\text{ V}$	-	60	-	ns
Q_{rr}	Reverse recovery charge		-	0.30	-	μC

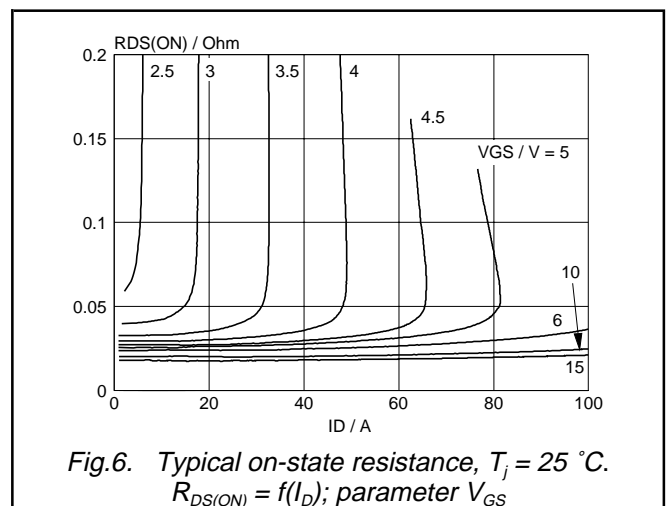
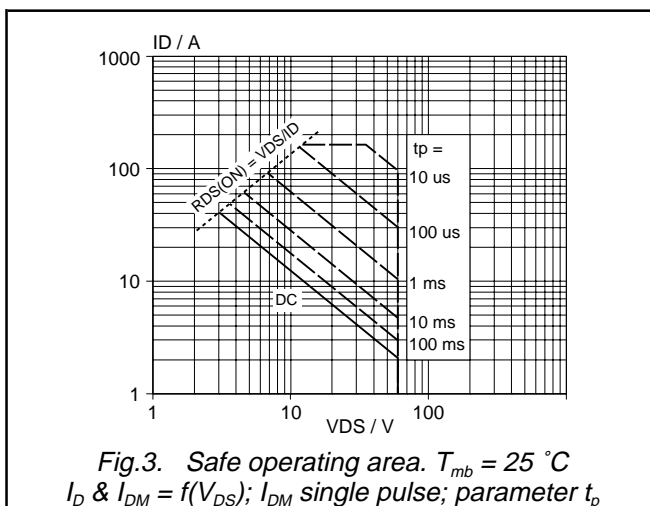
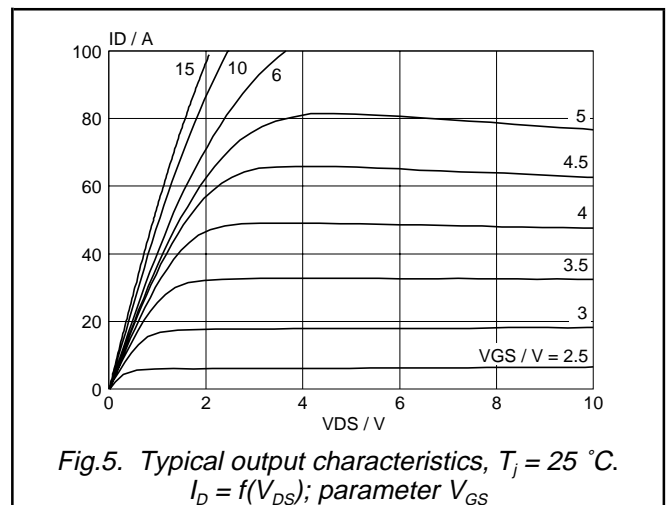
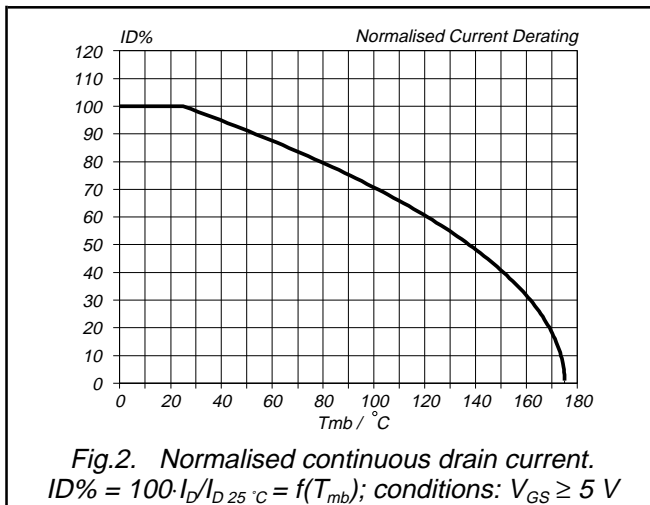
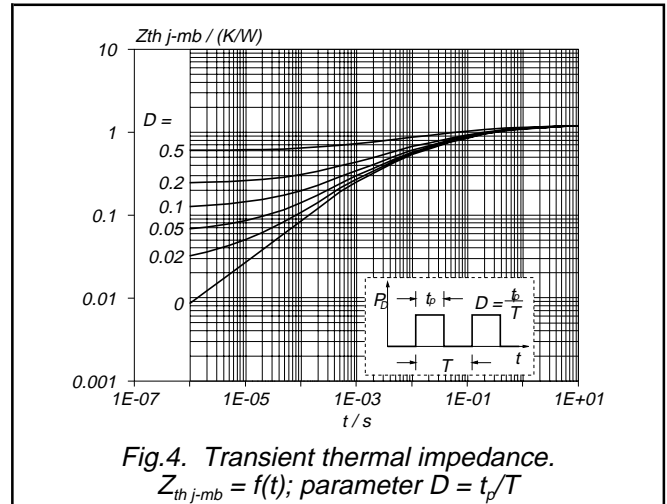
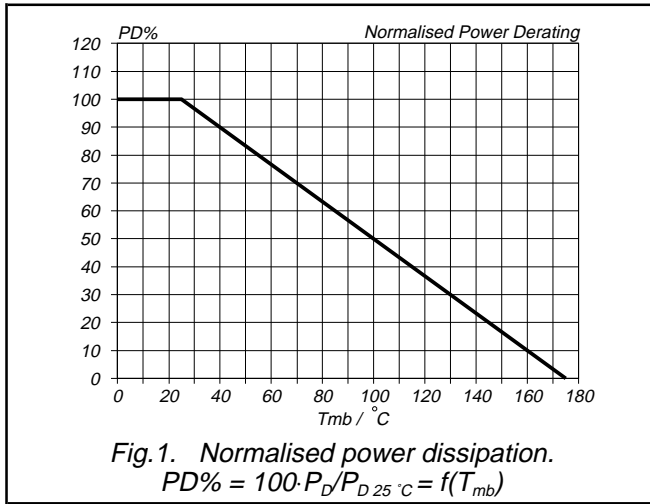
AVALANCHE LIMITING VALUE

 $T_{mb} = 25\text{ °C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
W_{DSS}	Drain-source non-repetitive unclamped inductive turn-off energy	$I_D = 41\text{ A}; V_{DD} \leq 25\text{ V};$ $V_{GS} = 5\text{ V}; R_{GS} = 50\ \Omega$	-	-	90	mJ

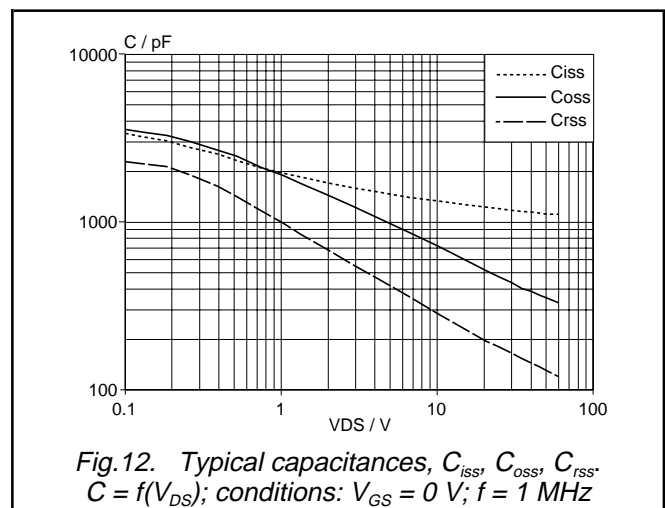
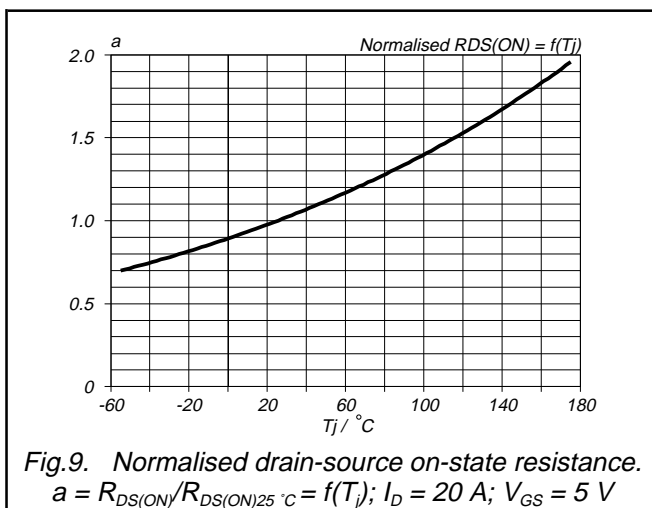
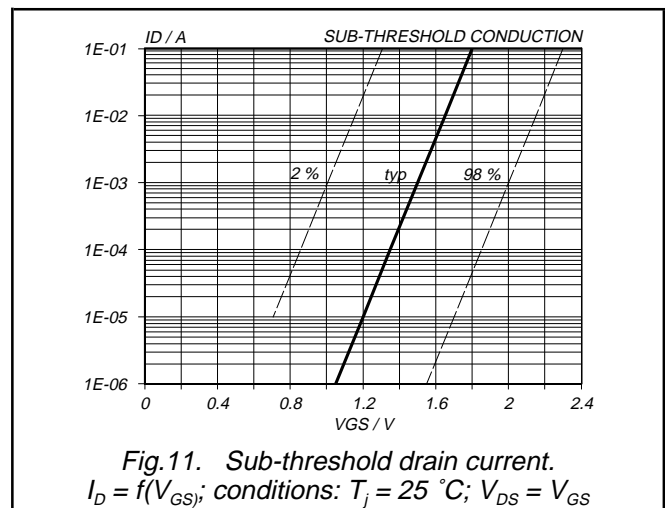
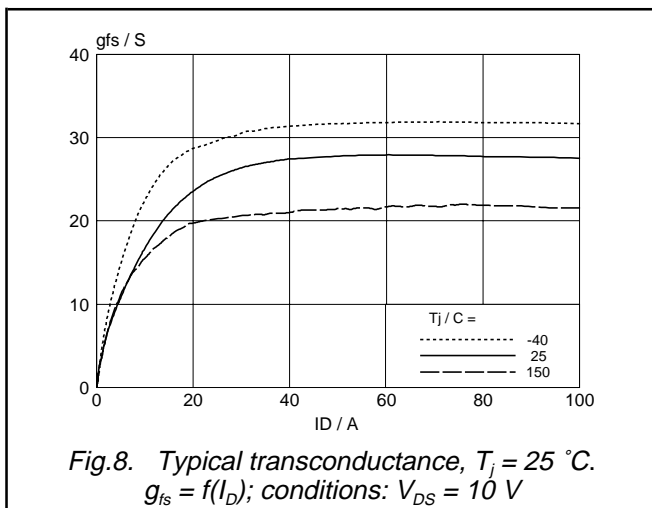
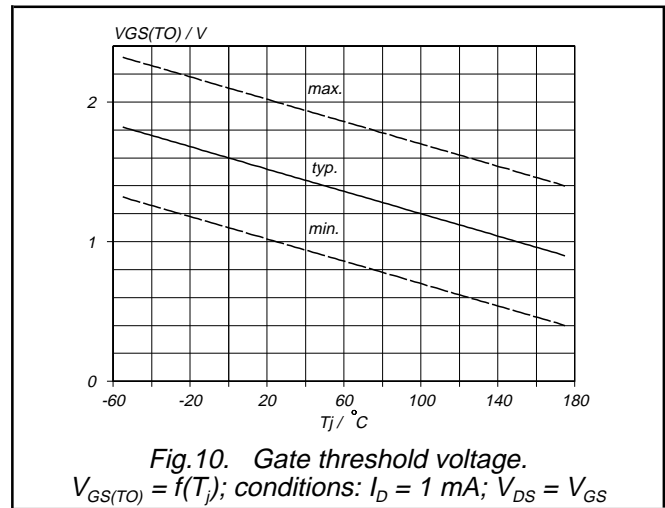
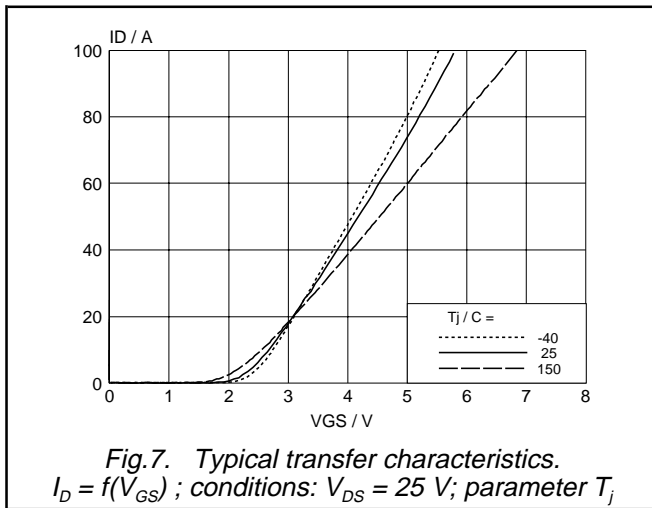
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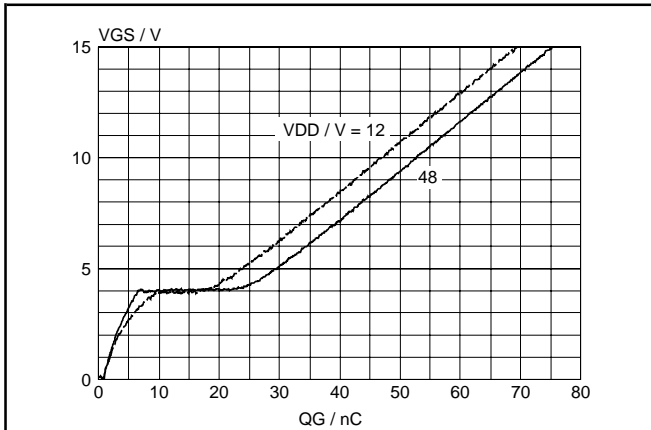


Fig. 13. Typical turn-on gate-charge characteristics.
 $V_{GS} = f(Q_G)$; conditions: $I_D = 41\text{ A}$; parameter V_{DS}

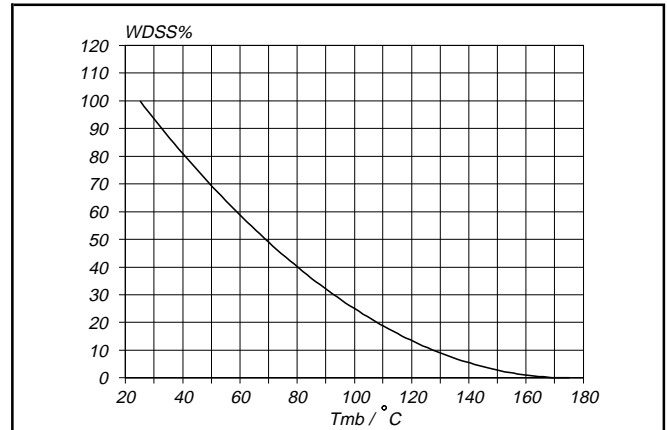


Fig. 15. Normalised avalanche energy rating.
 $W_{DSS}\% = f(T_{mb})$; conditions: $I_D = 41\text{ A}$

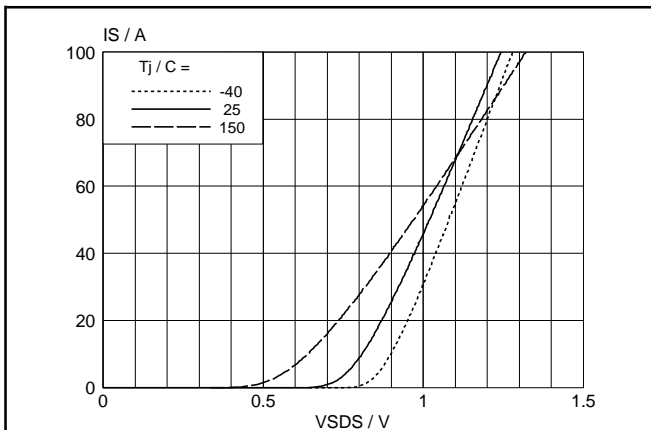


Fig. 14. Typical reverse diode current.
 $I_F = f(V_{SDS})$; conditions: $V_{GS} = 0\text{ V}$; parameter T_j

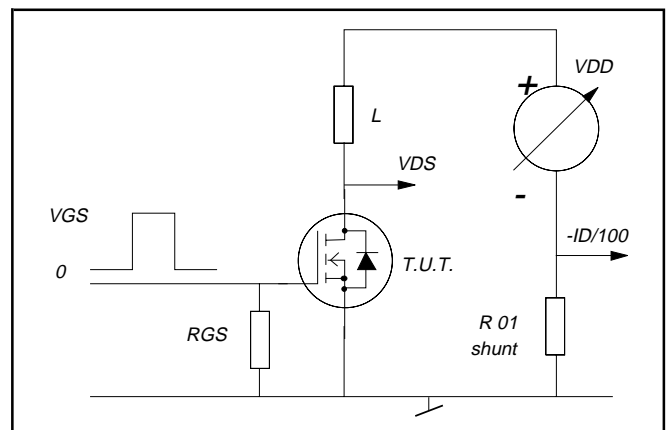


Fig. 16. Avalanche energy test circuit.
 $W_{DSS} = 0.5 \cdot L I_D^2 \cdot BV_{DSS} / (BV_{DSS} - V_{DD})$

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MECHANICAL DATA

Dimensions in mm

Net Mass: 1.4 g

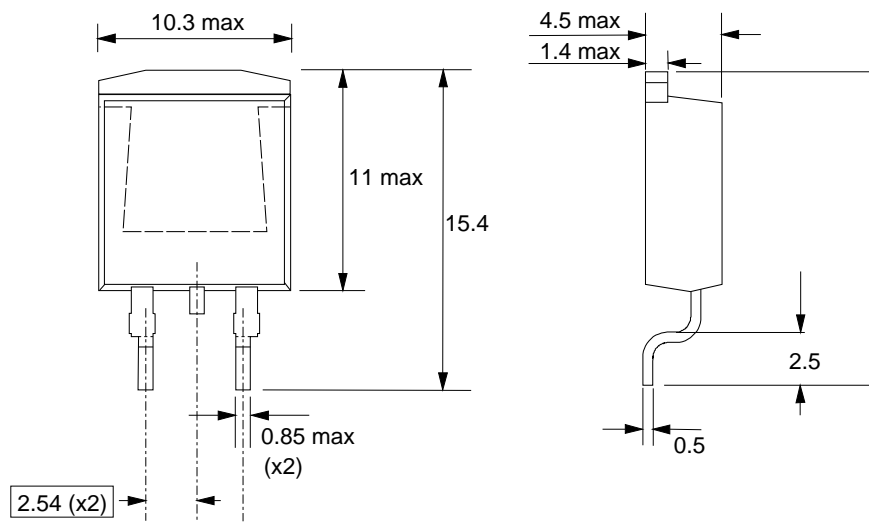


Fig.17. SOT404 : centre pin connected to mounting base.

MOUNTING INSTRUCTIONS

Dimensions in mm

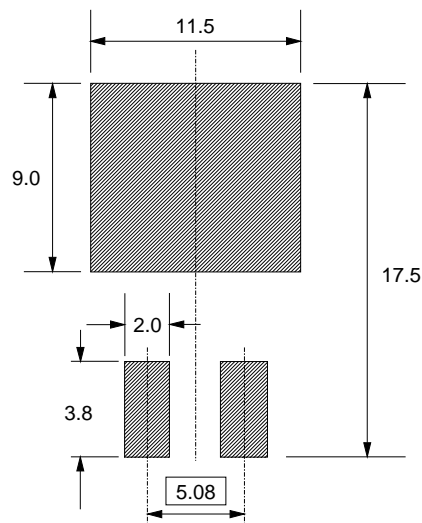


Fig.18. SOT404 : soldering pattern for surface mounting.

Notes

1. Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
2. Epoxy meets UL94 V0 at 1/8".

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BUK565-60H**DEFINITIONS**

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	
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